

MMBF4416LT1

Preferred Device

JFET VHF/UHF Amplifier Transistor

N-Channel

Features

- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Gate Current	I_G	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

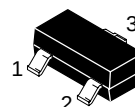
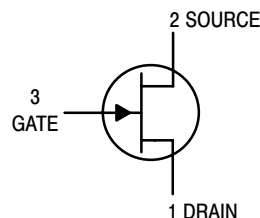
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.



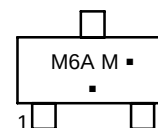
ON Semiconductor®

<http://onsemi.com>



SOT-23 (TO-236)
CASE 318
STYLE 10

MARKING DIAGRAM



M6A = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBF4416LT1	SOT-23	3,000 / Tape & Reel
MMBF4416LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MMBF4416LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu\text{Adc}$, $V_{DS} = 0$)	$V_{(BR)GSS}$	30	–	Vdc
Gate Reverse Current ($V_{GS} = 20\ \text{Vdc}$, $V_{DS} = 0$) ($V_{GS} = 20\ \text{Vdc}$, $V_{DS} = 0$, $T_A = 150^\circ\text{C}$)	I_{GSS}	–	1.0 200	nAdc
Gate Source Cutoff Voltage ($I_D = 1.0\ \text{nAdc}$, $V_{DS} = 15\ \text{Vdc}$)	$V_{GS(off)}$	–	–6.0	Vdc
Gate Source Voltage ($I_D = 0.5\ \text{mAdc}$, $V_{DS} = 15\ \text{Vdc}$)	V_{GS}	–1.0	–5.5	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current ($V_{GS} = 15\ \text{Vdc}$, $V_{GS} = 0$)	I_{DSS}	5.0	15	mAdc
Gate-Source Forward Voltage ($I_G = 1.0\ \text{mAdc}$, $V_{DS} = 0$)	$V_{GS(f)}$	–	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{kHz}$)	$ Y_{fs} $	4500	7500	μmhos
Output Admittance ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{kHz}$)	$ Y_{os} $	–	50	μmhos
Input Capacitance ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{iss}	–	4.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 10\ \text{MHz}$)	C_{rss}	–	0.8	pF
Output Capacitance ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{oss}	–	2.0	pF

COMMON SOURCE CHARACTERISTICS ADMITTANCE PARAMETERS

($V_{DS} = 15\ \text{Vdc}$, $T_{\text{channel}} = 25^\circ\text{C}$)

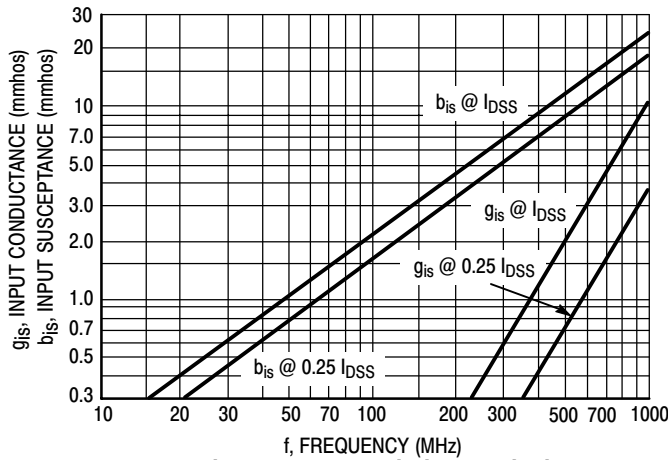


Figure 1. Input Admittance (Y_{is})

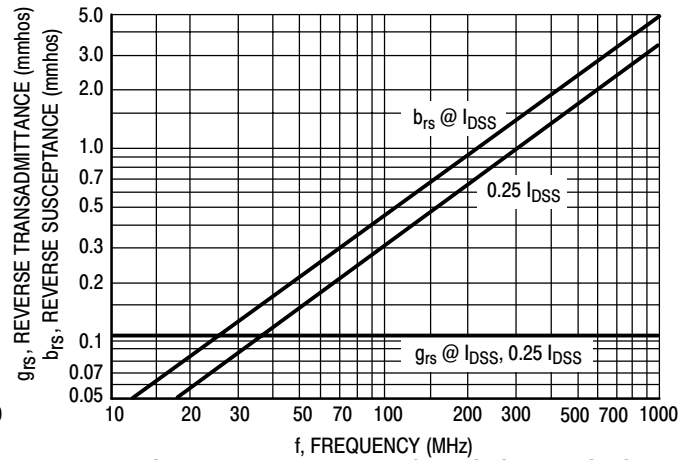


Figure 2. Reverse Transfer Admittance (Y_{rs})

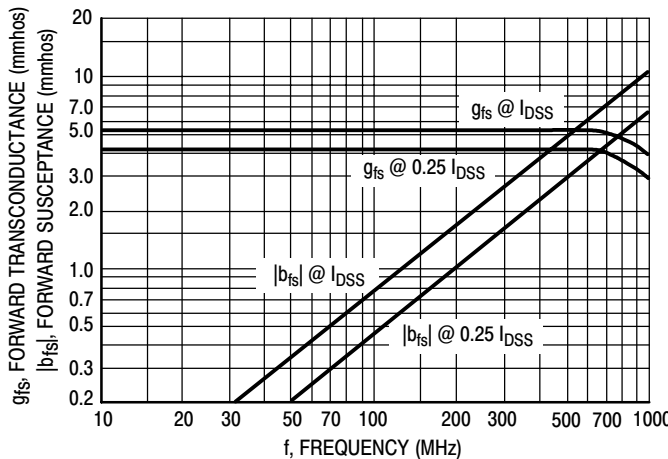


Figure 3. Forward Transadmittance (Y_{fs})

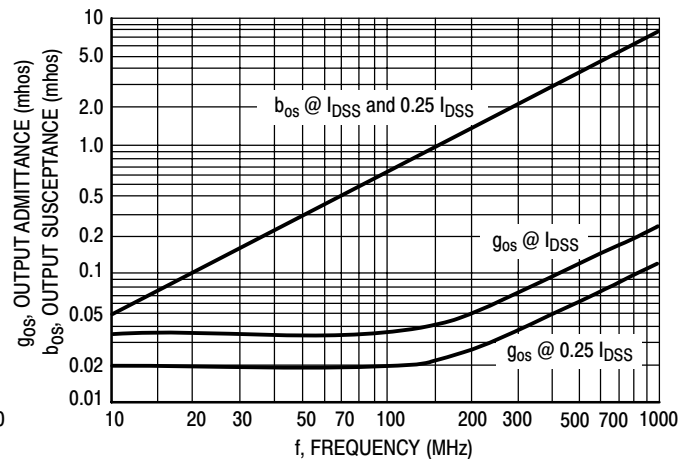
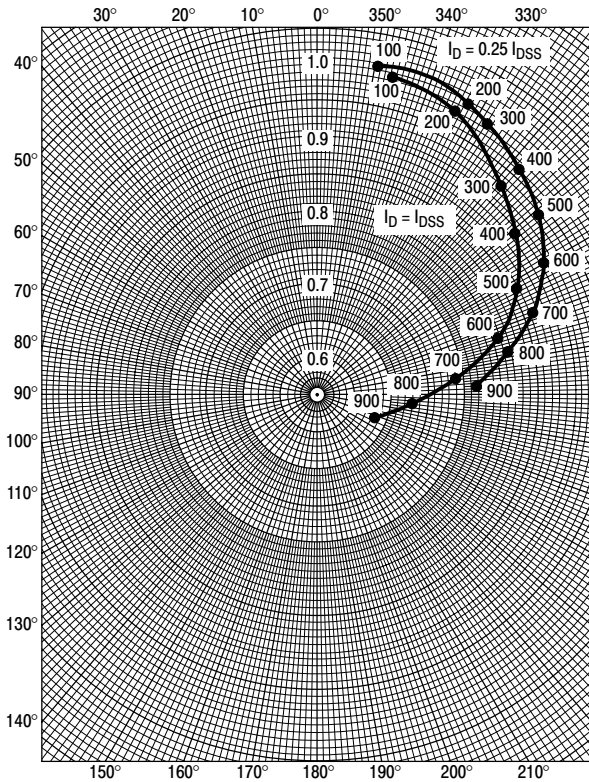
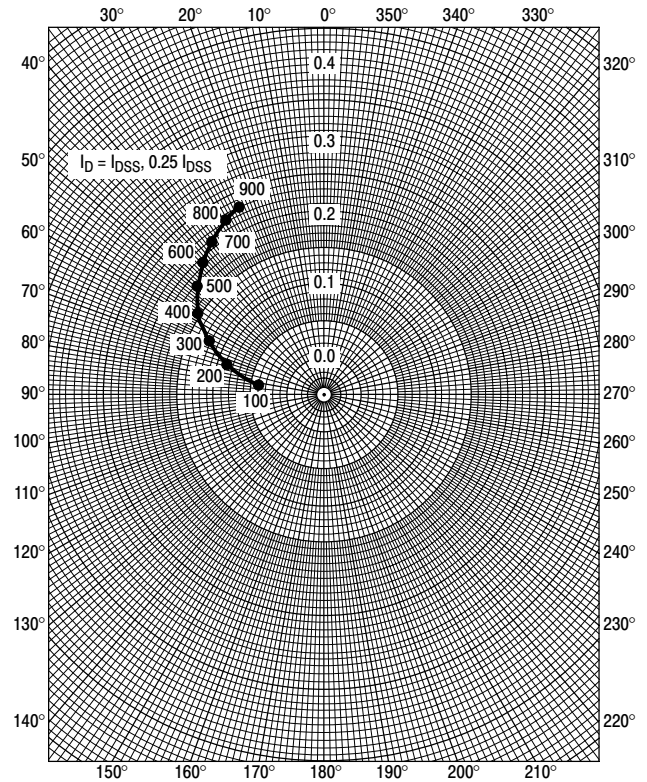
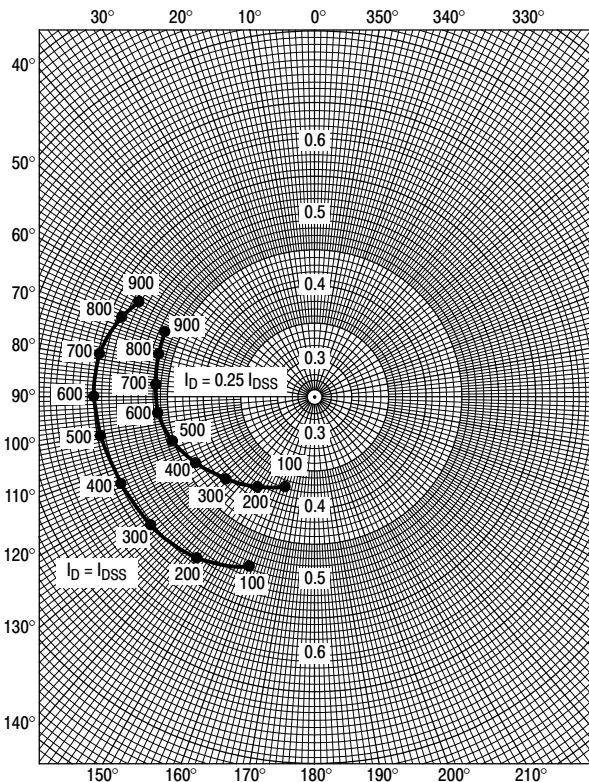
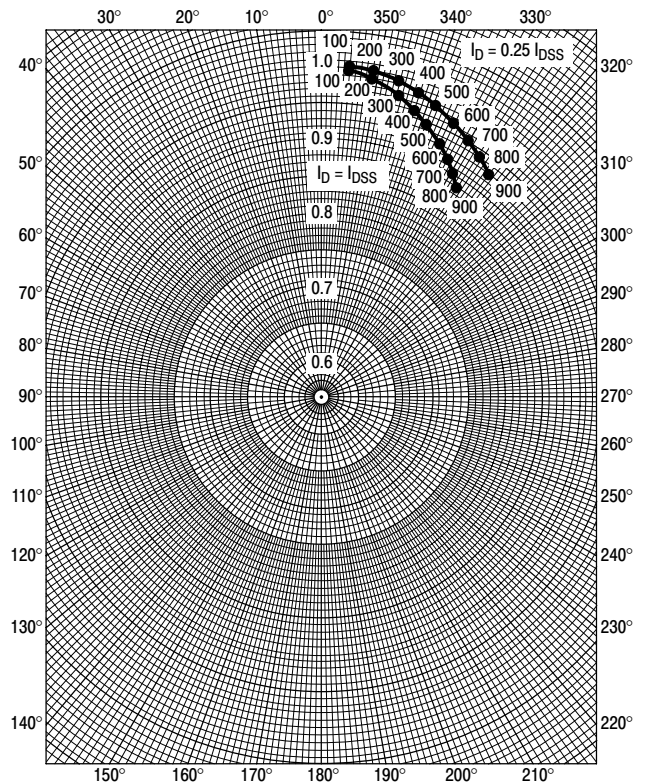


Figure 4. Output Admittance (Y_{os})

COMMON SOURCE CHARACTERISTICS

S-PARAMETERS

(V_{DS} = 15 Vdc, T_{channel} = 25°C, Data Points in MHz)Figure 5. S_{11s}Figure 6. S_{12s}Figure 7. S_{21s}Figure 8. S_{22s}

COMMON GATE CHARACTERISTICS ADMITTANCE PARAMETERS

($V_{DG} = 15 \text{ Vdc}$, $T_{\text{channel}} = 25^\circ\text{C}$)

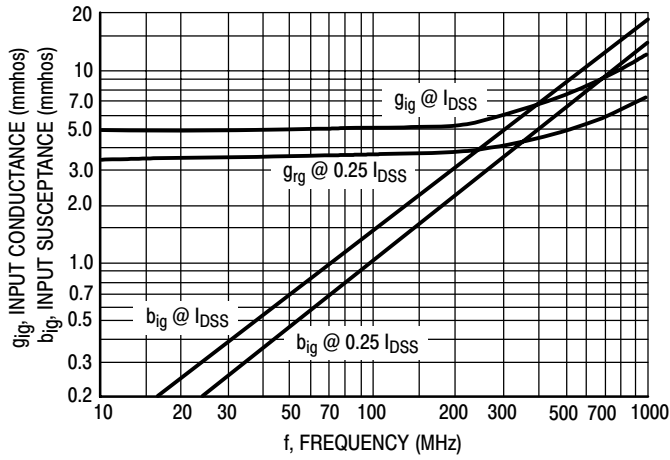


Figure 9. Input Admittance (y_{ig})

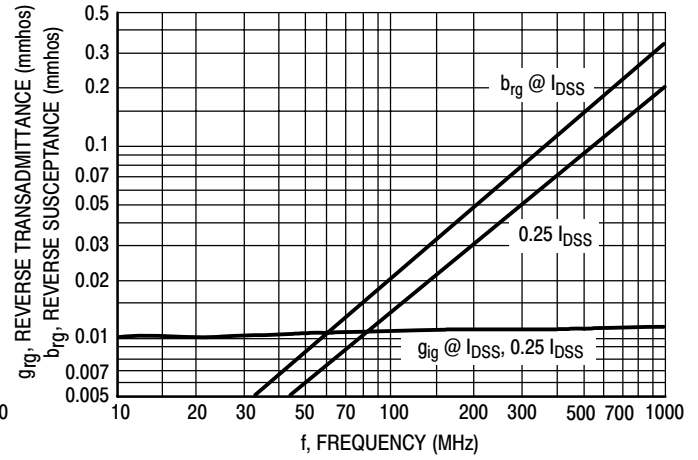


Figure 10. Reverse Transfer Admittance (y_{rg})

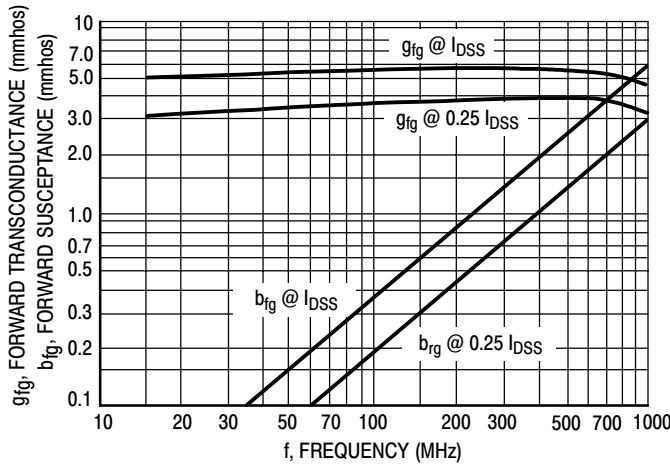


Figure 11. Forward Transfer Admittance (y_{fg})

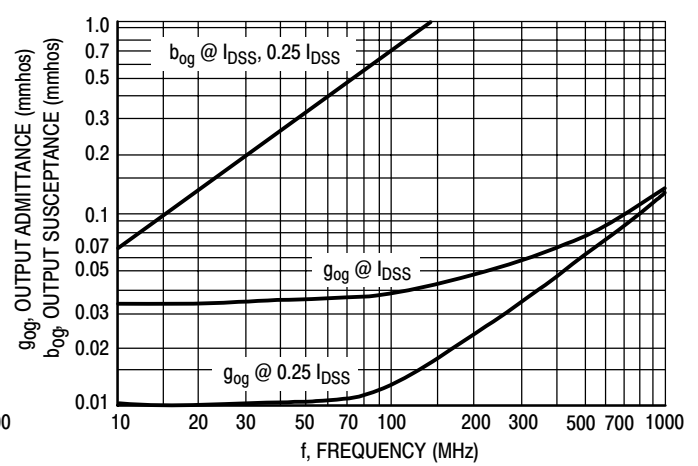


Figure 12. Output Admittance (y_{og})

COMMON GATE CHARACTERISTICS

S-PARAMETERS

($V_{DS} = 15\text{ Vdc}$, $T_{\text{channel}} = 25^\circ\text{C}$, Data Points in MHz)

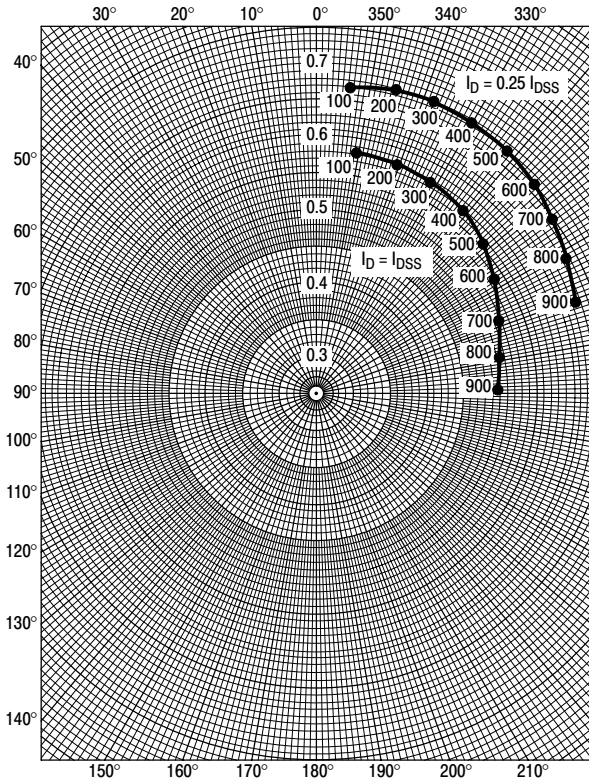


Figure 13. S_{11g}

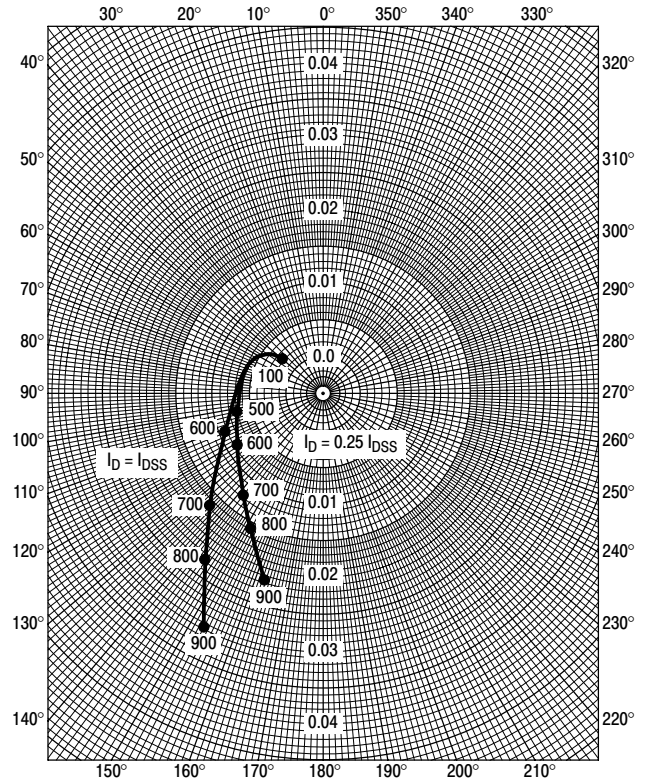


Figure 14. S_{12g}

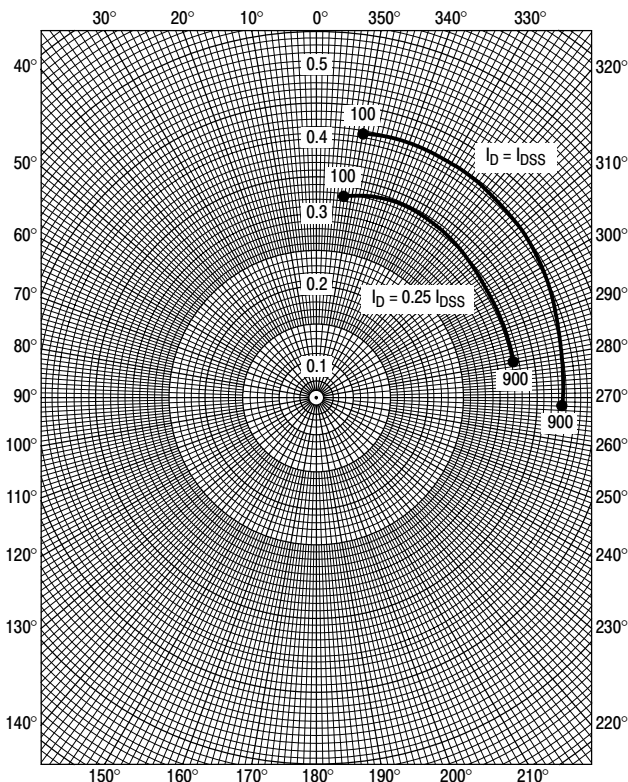


Figure 15. S_{21g}

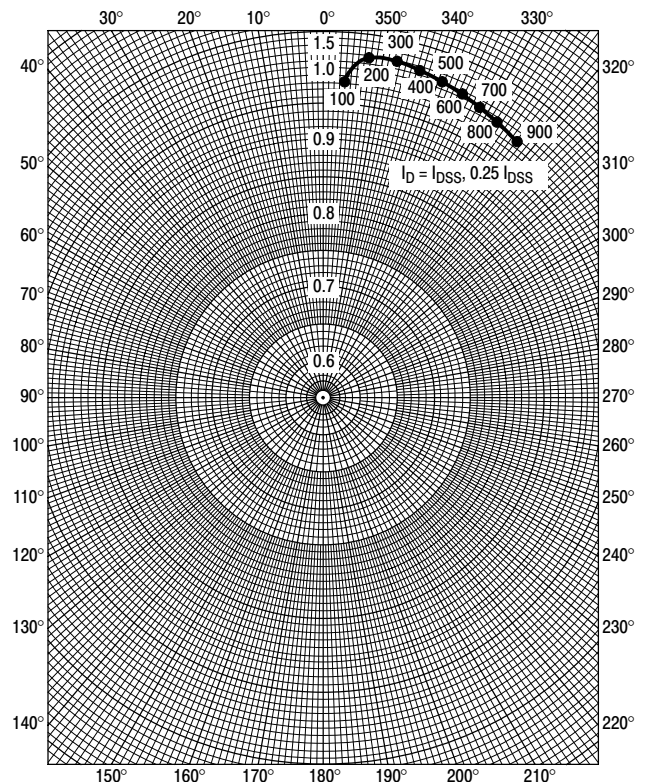
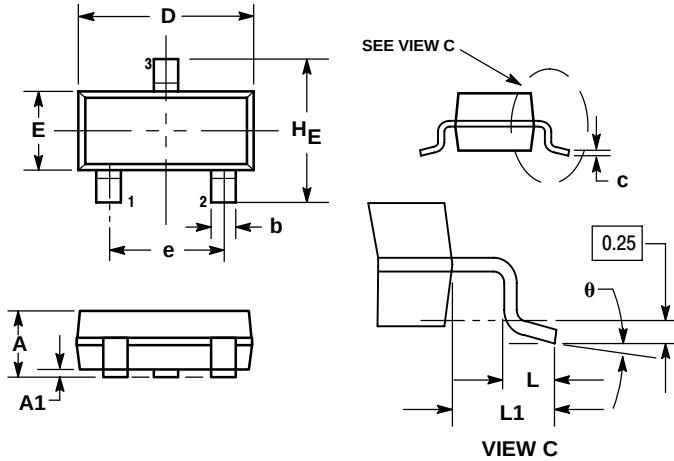


Figure 16. S_{22g}

MMBF4416LT1

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AN



NOTES:

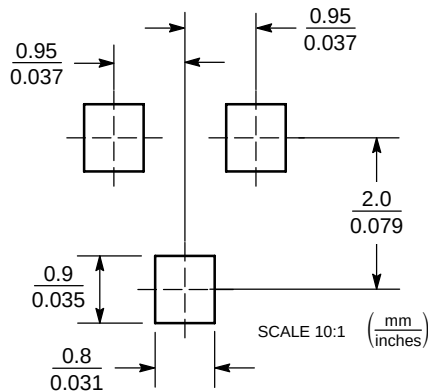
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 10:

1. DRAIN
2. SOURCE
3. GATE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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